

STARPOWER

SEMICONDUCTOR

IGBT

GD200HFU120C8S

1200V/200A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra switching speed as well as short circuit ruggedness. They are designed for the applications such as electronic welder and inductive heating.

Features

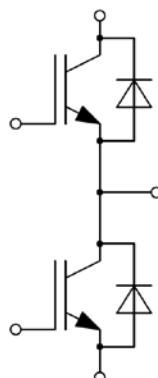
- NPT IGBT technology
- 10 μ s short circuit capability
- Low switching losses
- $V_{CE(sat)}$ with positive temperature coefficient
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology



Typical Applications

- Switching mode power supply
- Inductive heating
- Electronic welder

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

| Symbol | Description | Value | Unit |
|-----------|---|----------|------|
| V_{CES} | Collector-Emitter Voltage | 1200 | V |
| V_{GES} | Gate-Emitter Voltage | ± 20 | V |
| I_C | Collector Current @ $T_C=25^{\circ}\text{C}$ | 262 | A |
| | @ $T_C=65^{\circ}\text{C}$ | 200 | |
| I_{CM} | Pulsed Collector Current $t_p=1\text{ms}$ | 400 | A |
| P_D | Maximum Power Dissipation @ $T_j=150^{\circ}\text{C}$ | 1315 | W |

Diode

| Symbol | Description | Value | Unit |
|-----------|--|-------|------|
| V_{RRM} | Repetitive Peak Reverse Voltage | 1200 | V |
| I_F | Diode Continuous Forward Current | 200 | A |
| I_{FM} | Diode Maximum Forward Current $t_p=1\text{ms}$ | 400 | A |

Module

| Symbol | Description | Value | Unit |
|------------|--|-------------|--------------------|
| T_{jmax} | Maximum Junction Temperature | 150 | $^{\circ}\text{C}$ |
| T_{jop} | Operating Junction Temperature | -40 to +125 | $^{\circ}\text{C}$ |
| T_{STG} | Storage Temperature Range | -40 to +125 | $^{\circ}\text{C}$ |
| V_{ISO} | Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$ | 2500 | V |

IGBT Characteristics $T_C=25^\circ\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit | |
|---------------|---|---|------|------|------|---------------|----|
| $V_{CE(sat)}$ | Collector to Emitter Saturation Voltage | $I_C=200\text{A}, V_{GE}=15\text{V}, T_j=25^\circ\text{C}$ | | 3.00 | 3.45 | V | |
| | | $I_C=200\text{A}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}$ | | 3.80 | | | |
| $V_{GE(th)}$ | Gate-Emitter Threshold Voltage | $I_C=2.0\text{mA}, V_{CE}=V_{GE}, T_j=25^\circ\text{C}$ | 4.4 | 5.3 | 6.0 | V | |
| I_{CES} | Collector Cut-Off Current | $V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^\circ\text{C}$ | | | 5.0 | mA | |
| I_{GES} | Gate-Emitter Leakage Current | $V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^\circ\text{C}$ | | | 400 | nA | |
| R_{Gint} | Internal Gate Resistance | | | 1.3 | | Ω | |
| C_{ies} | Input Capacitance | | | 13.0 | | nF | |
| C_{res} | Reverse Transfer Capacitance | $V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$ | | 0.85 | | nF | |
| Q_G | Gate Charge | $V_{GE}=-15\dots+15\text{V}$ | | 2.10 | | μC | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{CC}=600\text{V}, I_C=200\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=25^\circ\text{C}$ | | 87 | | ns | |
| t_r | Rise Time | | | 40 | | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 451 | | ns | |
| t_f | Fall Time | | | 63 | | ns | |
| E_{on} | Turn-On Switching Loss | | | | 6.8 | | mJ |
| E_{off} | Turn-Off Switching Loss | | | | 11.9 | | mJ |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{CC}=600\text{V}, I_C=200\text{A}, R_G=4.7\Omega, V_{GE}=\pm 15\text{V}, T_j=125^\circ\text{C}$ | | 88 | | ns | |
| t_r | Rise Time | | | 44 | | ns | |
| $t_{d(off)}$ | Turn-Off Delay Time | | | 483 | | ns | |
| t_f | Fall Time | | | 78 | | ns | |
| E_{on} | Turn-On Switching Loss | | | | 11.4 | | mJ |
| E_{off} | Turn-Off Switching Loss | | | | 13.5 | | mJ |
| I_{SC} | SC Data | $t_P \leq 10\mu\text{s}, V_{GE}=15\text{V}, T_j=125^\circ\text{C}, V_{CC}=900\text{V}, V_{CEM} \leq 1200\text{V}$ | | 1300 | | A | |

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

| Symbol | Parameter | Test Conditions | Min. | Typ. | Max. | Unit |
|-----------|-------------------------------|---|------|------|------|---------------|
| V_F | Diode Forward Voltage | $I_F=200\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$ | | 1.95 | 2.40 | V |
| | | $I_F=200\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$ | | 2.00 | | |
| Q_r | Recovered Charge | $V_R=600\text{V}, I_F=200\text{A},$ $-di/dt=4600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$ | | 13.3 | | μC |
| I_{RM} | Peak Reverse Recovery Current | | | 236 | | A |
| E_{rec} | Reverse Recovery Energy | | | 6.6 | | mJ |
| Q_r | Recovered Charge | | | 23.0 | | μC |
| I_{RM} | Peak Reverse Recovery Current | $V_R=600\text{V}, I_F=200\text{A},$ $-di/dt=4600\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$ | | 269 | | A |
| E_{rec} | Reverse Recovery Energy | | | 10.5 | | mJ |

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

| Symbol | Parameter | Min. | Typ. | Max. | Unit |
|------------|--------------------------------------|------|-------|-------|------|
| R_{thJC} | Junction-to-Case (per IGBT) | | | 0.095 | K/W |
| | Junction-to-Case (per Diode) | | | 0.202 | |
| R_{thCH} | Case-to-Heatsink (per IGBT) | | 0.135 | | K/W |
| | Case-to-Heatsink (per Diode) | | 0.288 | | |
| | Case-to-Heatsink (per Module) | | 0.046 | | |
| M | Terminal Connection Torque, Screw M5 | 2.5 | | 5.0 | N.m |
| | Mounting Torque, Screw M6 | 3.0 | | 5.0 | |
| G | Weight of Module | | 200 | | g |

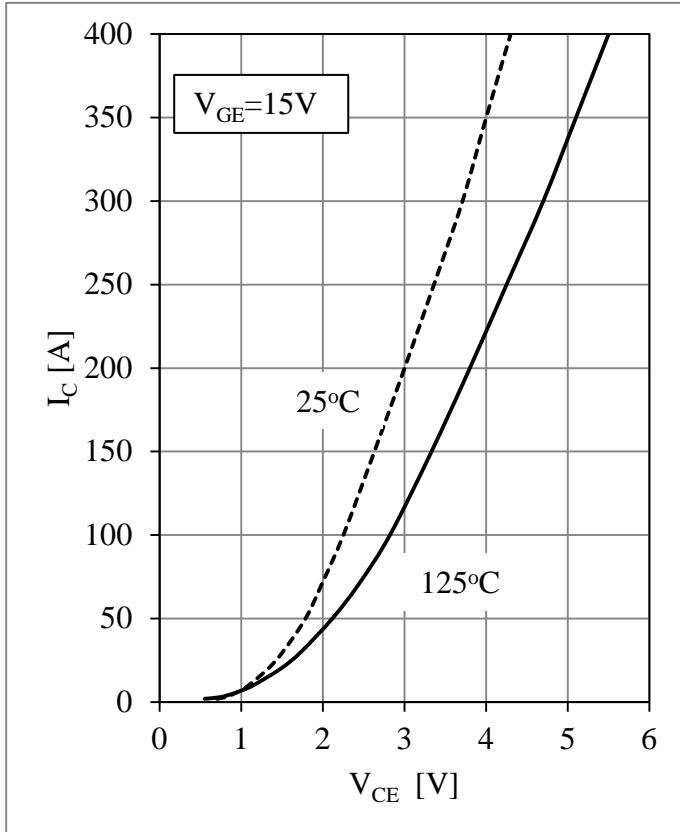


Fig 1. IGBT Output Characteristics

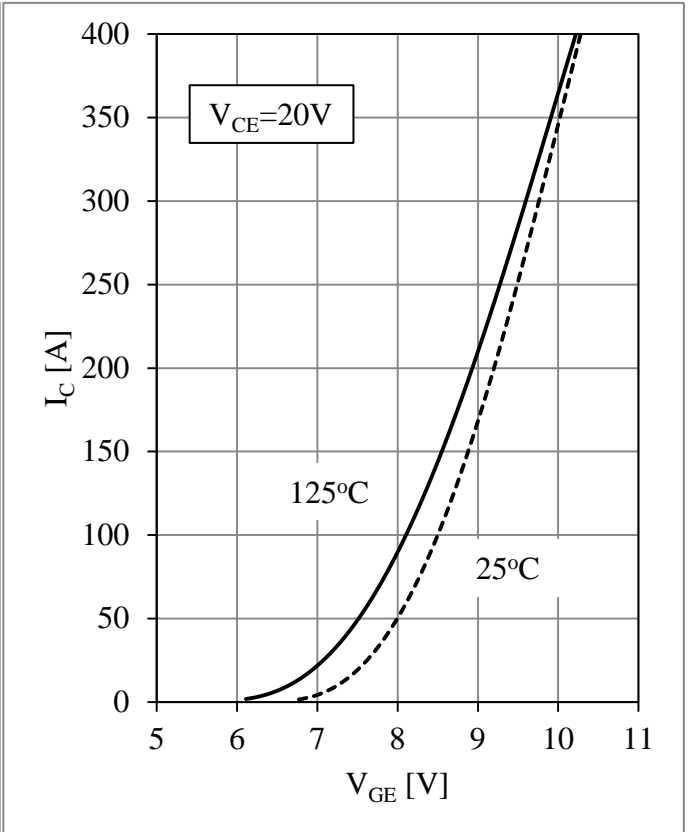


Fig 2. IGBT Transfer Characteristics

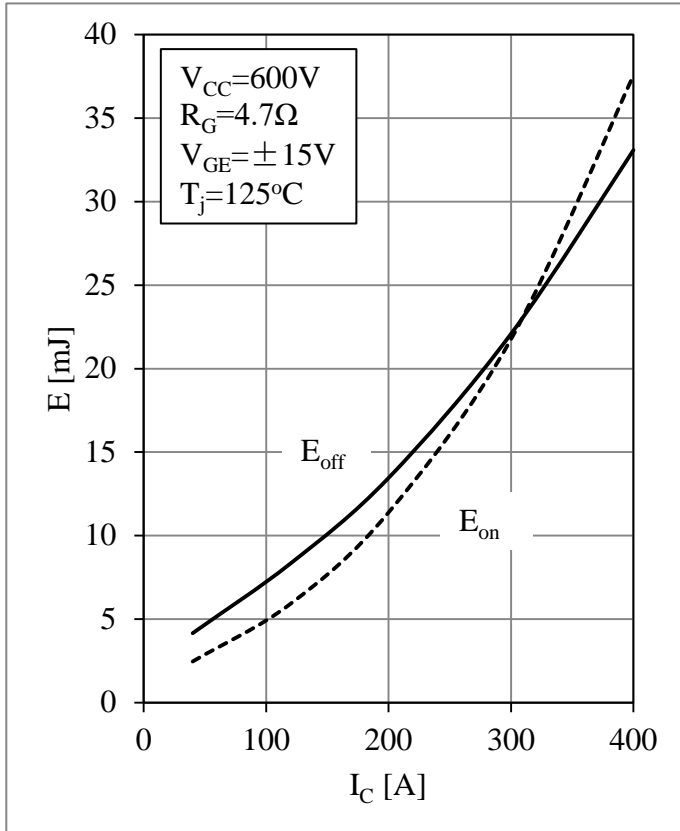


Fig 3. IGBT Switching Loss vs. I_C

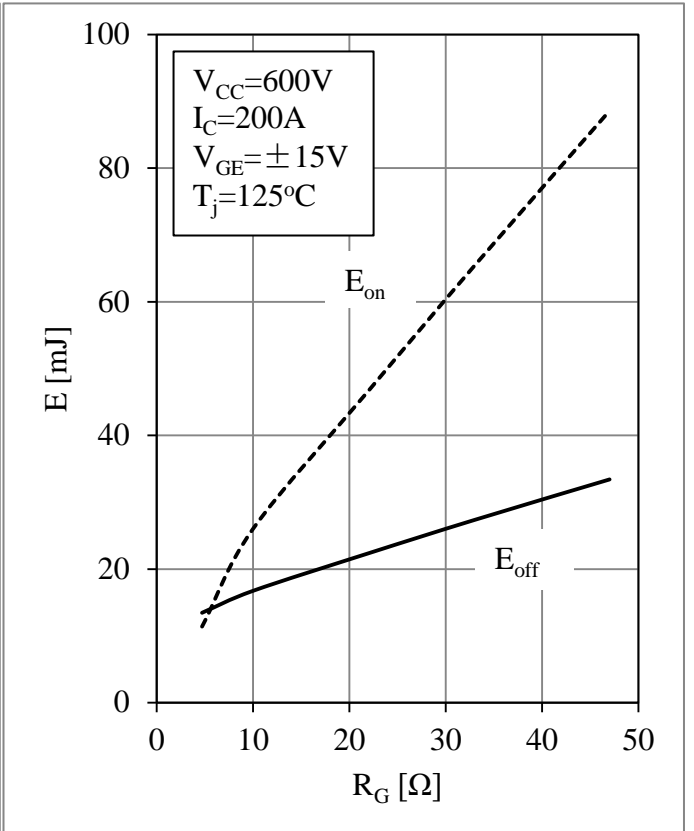


Fig 4. IGBT Switching Loss vs. R_G

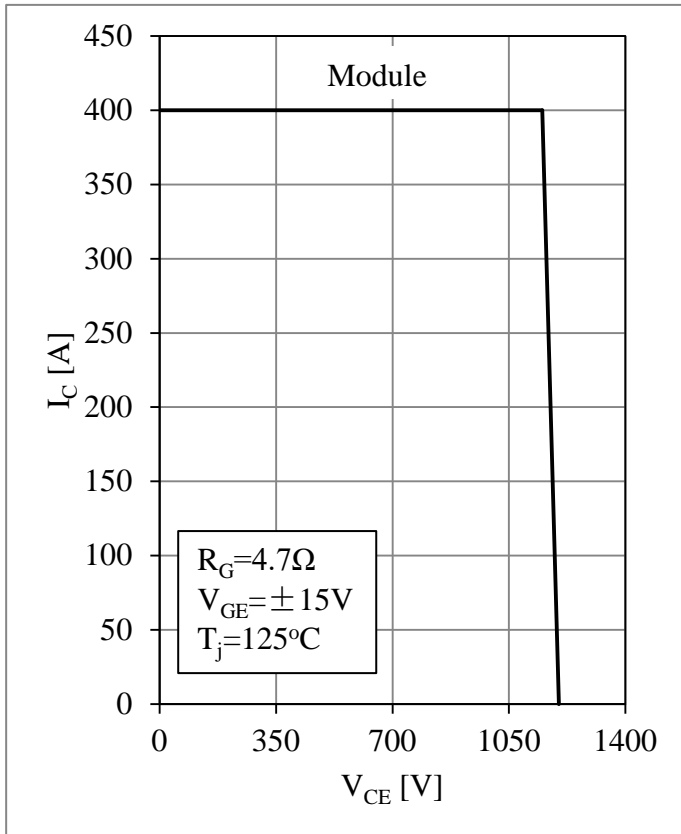


Fig 5. RBSOA

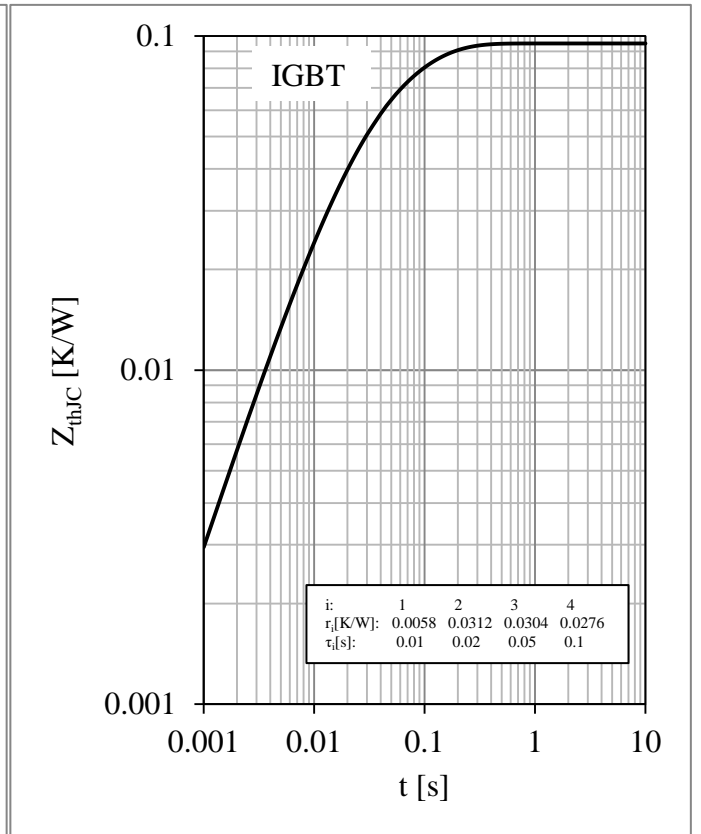


Fig 6. IGBT Transient Thermal Impedance

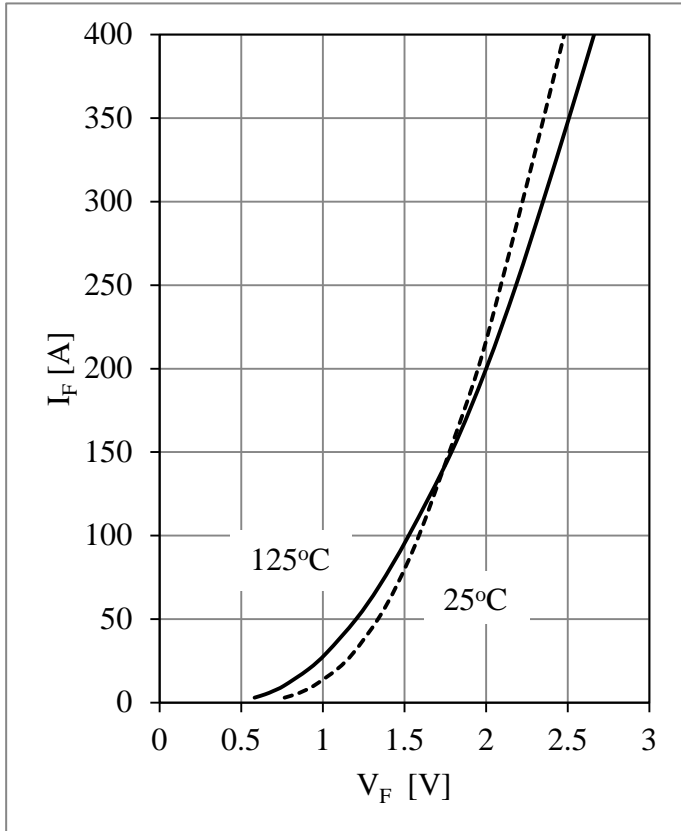


Fig 7. Diode Forward Characteristics

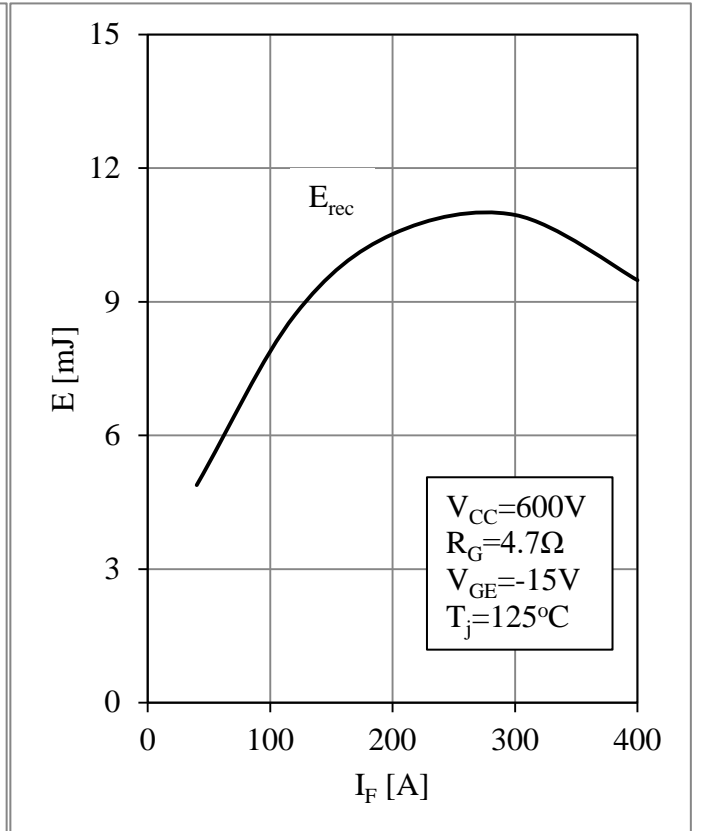


Fig 8. Diode Switching Loss vs. I_F

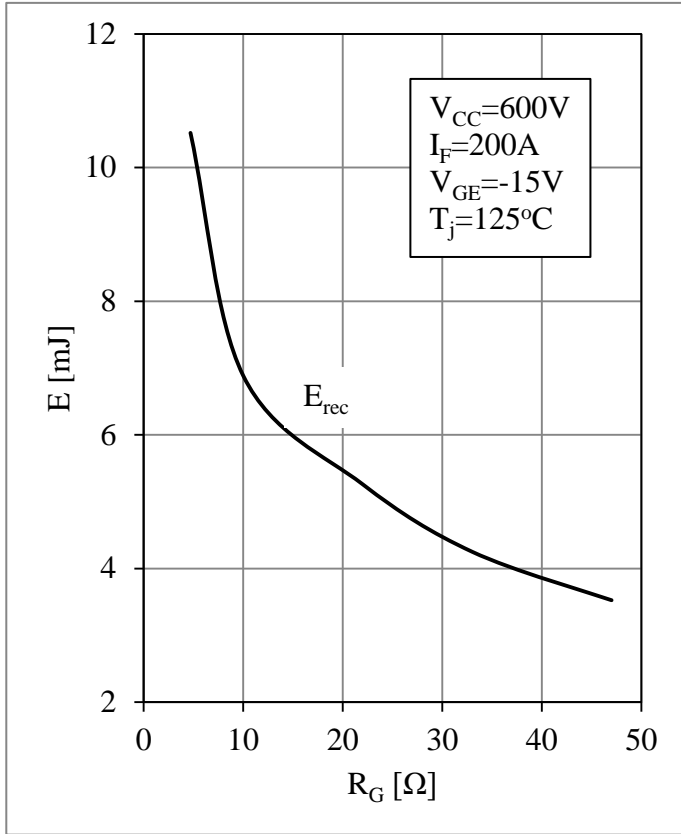


Fig 9. Diode Switching Loss vs. R_G

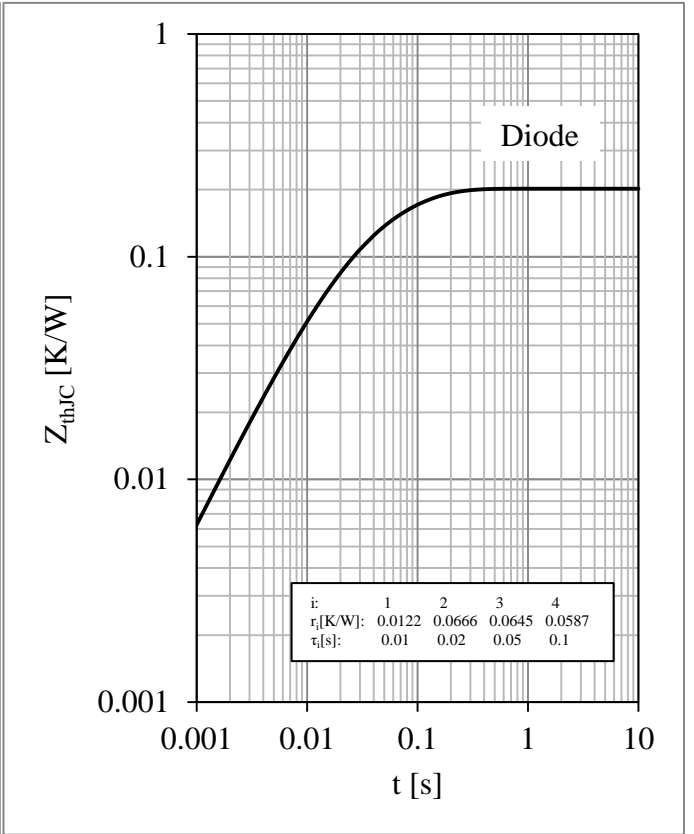
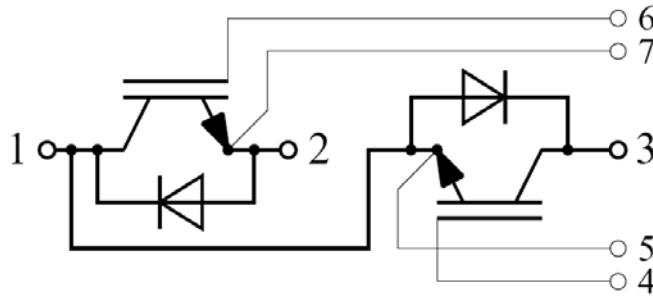


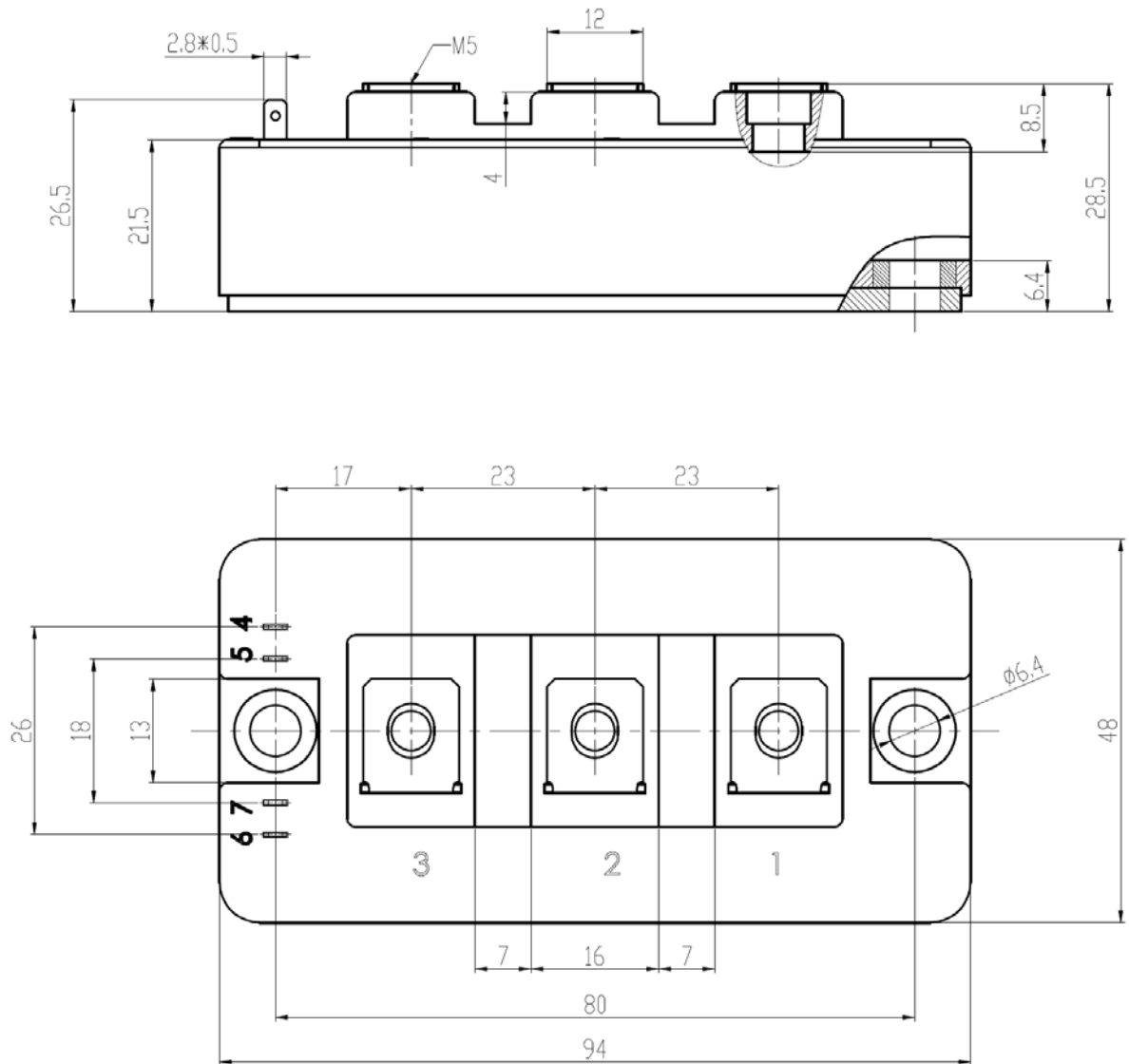
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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